

ZHEN

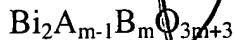
Serial No. 09/842,631

Please add the following new claim 29:

--29. {NEW} A semiconductor device fabricating method as claimed in claim 26,

wherein

the ferroelectric thin film is made of a material expressed by:



where A represents one selected from a group consisting of Na, K, Pb, Ca, Sr, Ba and Bi,

B represents one selected from a group consisting of Fe, Ti, Nb, Ta, W and Mo, and m

represents a natural number.

REMARKS

The above amendments are made to place the claims in a more traditional format.

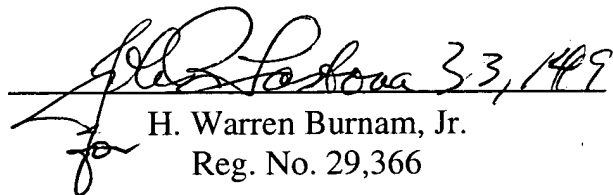
Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned "**Version With Markings To Show Changes Made.**"

Respectfully submitted,

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July 9, 2001

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